

THE SPECIFICATION OF AlGaAs IR LED CHIP "IR4J"

1. DESCRIPTION

This is a AlGaAs Infrared LED chip. It is N-side up. The peak wavelength is 875 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V_F) IF=20mA		1.4		V
Reverse Voltage (V_R) IR=10uA	5			V
Radiated Power ¹⁾ (P_o) IF=20mA	3.8			mW
Peak Wavelength (λ_p) IF=20mA		875		nm
Spectral Radiation Bandwidth ($\Delta\lambda$) IF=20mA		45		nm
Rise Time (T_r) Ifp=100mA Tw=125ns,Duty=25%		15	35	ns
Fall Time (T_f) Ifp=100mA Tw=125ns,Duty=25%		20	35	ns
PeakForward Voltage (V_{fm}) Ifp=400mA Tw=100 μ s,Duty=10%		2.20	2.5	V

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current	: 100 mA(DC)
Continuous Maximum Pulse Current	: 400 mA (Tw=100us,Duty=10%,Tj<120 deg.C)
Reverse Voltage	: 5 V(IR=10uA)
Operating Temperature	: -30 to 85 deg. C
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

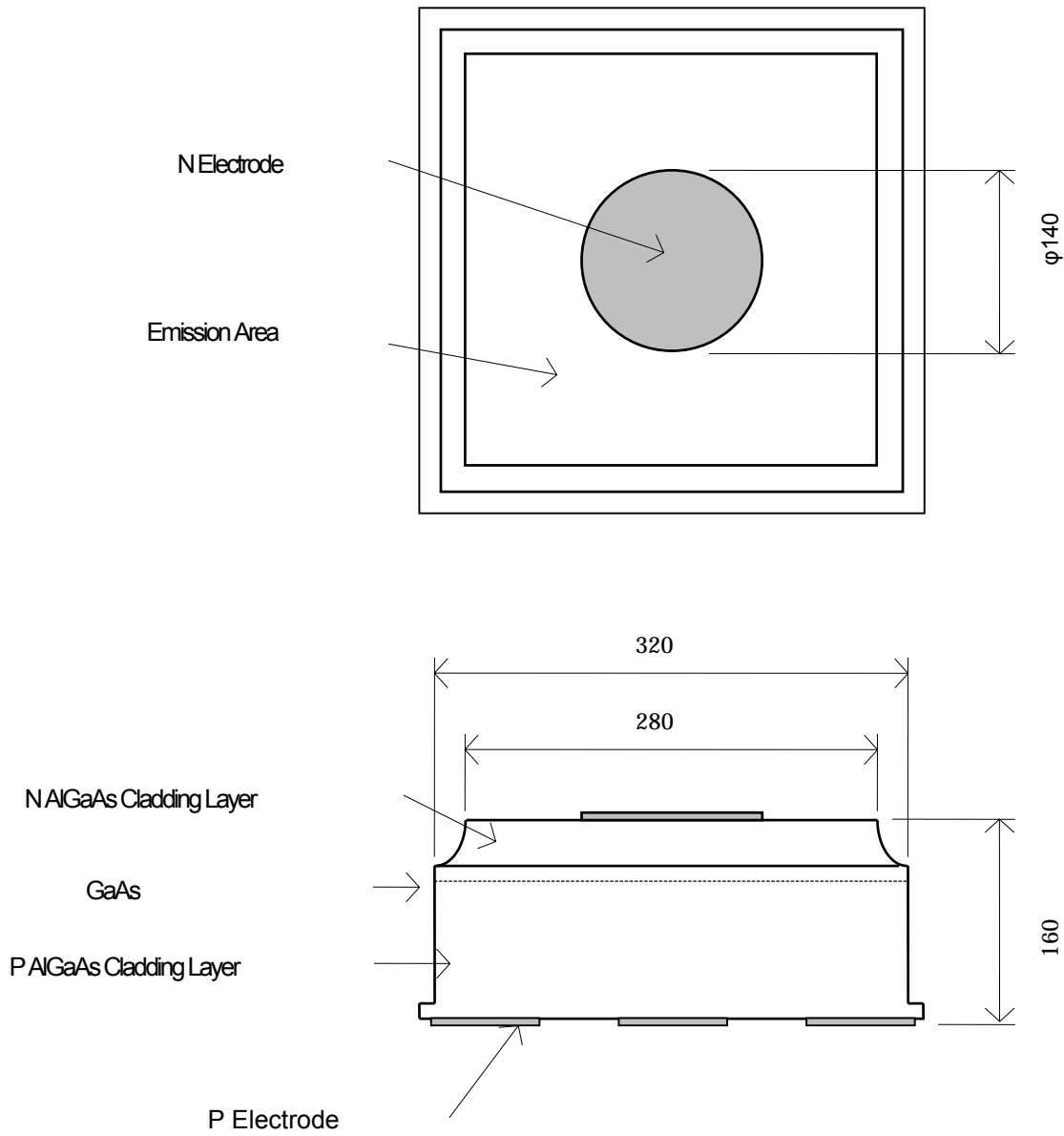
4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material	: AlGaAs
2)Structure	: Double Hetero Structure
3)Junction Size	: 0.320mm x 0.320mm
4)Thickness	: 0.160mm
5)Bond Pad Size	: 0.140mm diameter
6)Anode Metallization	: Gold Alloy
7)Cathode Metallization	: Gold Alloy

Physical Dimensions

Model IR4J

Unit: μm



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.